Elektronische Bauelemente

BAS21T

0.4A , 250V

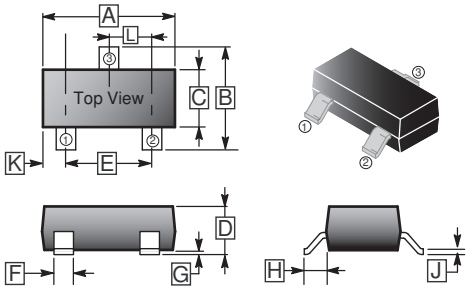
Plastic-Encapsulated Diode

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Fast switching speed
- For General Purpose Switching Applications
- High Conductance

SOT-523



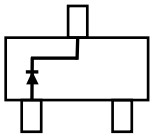
MARKING

T3

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-523	3K	7 inch

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.5	1.7	G	-	0.1
B	1.45	1.75	H	0.55 REF.	
C	0.75	0.85	J	0.1	0.2
D	0.7	0.9	K	-	
E	0.9	1.1	L	0.5 TYP.	
F	0.15	0.25	M	0.25	0.325



ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter		Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	250	V
Working Peak Reverse Voltage		V_{RWM}		
Reverse voltage		V_R		
Peak forward Continuous current		I_{FM}	400	mA
Maximum Average Forward Rectified Current		$I_{F(AV)}$	200	mA
Peak Forward Surge Current 8.3 ms Single Half Sine-Wave Super Imposed on Rated Load (JEDEC Method)	t=1.0μs	I_{FSM}	2.5	A
	t=1.0s		0.5	
Power dissipation		P_D	150	mW
Typical Thermal Resistance Junction to Ambient		$R_{\theta JA}$	833	℃ / W
Operating Junction and storage temperature range		T_J,T_{STG}	150, -65~150	℃

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ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	250	-	-	V	I_R=100μA
Forward Voltage	V_{F1}	-	-	1	V	I_F=100mA
	V_{F2}	-	-	1.25		I_F=200mA
Reverse Voltage Leakage Current	I_R	-	-	0.1	μA	V_R=200V
Total Capacitance	C_T	-	-	5	pF	V_R=0 , f=1MHz
Reverse Recovery Time	T_{RR}	-	-	50	nS	I_F=I_R=30mA, I_{RR}=0.1 x I_R, R_L=100Ω

RATINGS AND CHARACTERISTIC CURVES

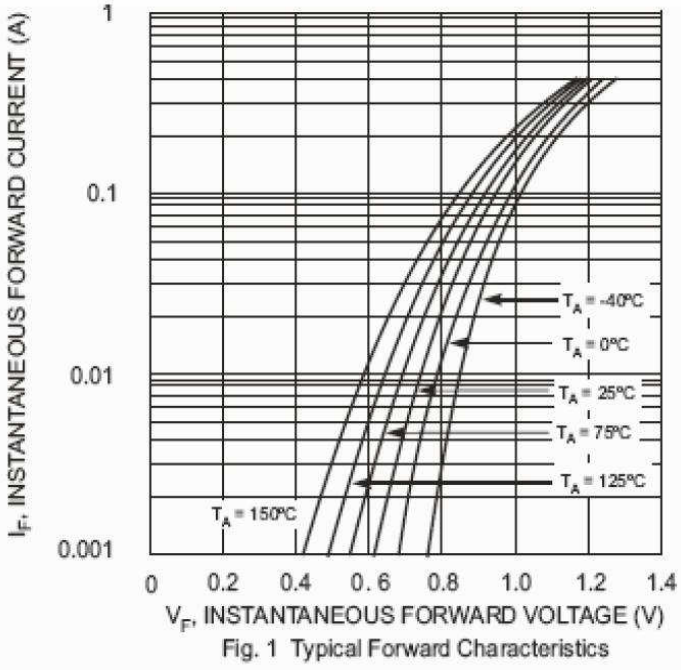

Fig. 1 Typical Forward Characteristics

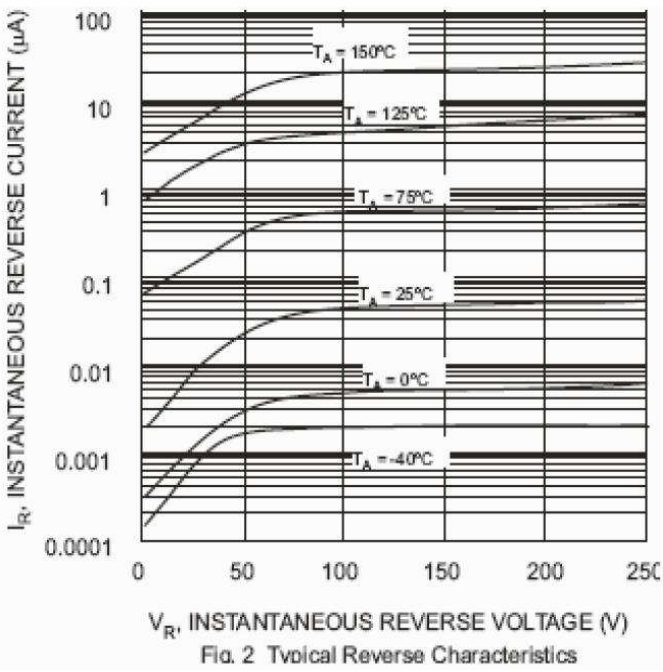

Fig. 2 Typical Reverse Characteristics